BLF879P; BLF879PS UHF power LDMOS transistor Rev. 4—1 September 2015

AMPLEON

Product data sheet

Product profile 1.

1.1 General description

A 500 W LDMOS RF power transistor for broadcast transmitter applications and industrial applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

Table 1. **Application information**

RF performance at $V_{DS} = 42 \text{ V}$ unless otherwise specified.

Mode of operation	f	P _{L(AV)}	P _{L(M)}	Gp	η _D	IMD3	IMD _{shldr}	PAR
	(MHz)	(W)	(W)	(dB)	(%)	(dBc)	(dBc)	(dB)
RF performance in a common source 860 MHz narrowband test circuit								
2-tone, class-AB	f ₁ = 860; f ₂ = 860.1	200	-	21	47	-33	-	-
DVB-T (8k OFDM)	858	95	-	21	33	-	–31 <u>[1]</u>	8.2 [2]
RF performance in a common source 470 MHz to 860 MHz broadband test circuit								
DVB-T (8k OFDM)	858	95	-	20	32	-	-32 <u>[1]</u>	8.0 [2]

^[1] Measured [dBc] with delta marker at 4.3 MHz from center frequency.

1.2 Features and benefits

- Excellent ruggedness
- Optimum thermal behavior and reliability, R_{th(j-c)} = 0.15 K/W
- High power gain
- High efficiency
- Designed for broadband operation (470 MHz to 860 MHz)
- Internal input matching for high gain and optimum broadband operation
- Excellent reliability
- Easy power control
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

1.3 Applications

- Communication transmitter applications in the UHF band
- Industrial applications in the UHF band

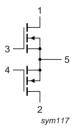
^[2] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF879P ((SOT539A)			
1	drain1			
2	drain2		1 2	1 . _
3	gate1		5	3
4	gate2		3 4	5
5	source	[1]		2 sym117
BLF879PS	S (SOT539B)			
1	drain1			





[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Name Description				
BLF879P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLF879PS	-	earless flanged balanced ceramic package; 4 leads	SOT539B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	104	V
V_{GS}	gate-source voltage		-0.5	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 80 °C; $P_{L(AV)}$ = 95 W	<u>11</u> 0.15	K/W

^[1] $R_{th(j-c)}$ is measured under RF conditions.

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.4 \text{ mA}$	[1]	104	-	-	V
V _{GS(th)}	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 240 mA	[1]	1.4	1.9	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 42 V		-	-	2.8	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$		-	38	-	Α
I_{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	280	nΑ
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 8.5 A$	[1]	-	120	-	mΩ
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 42 \text{ V};$ f = 1 MHz	[2]	-	210	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 42 \text{ V};$ f = 1 MHz		-	72	-	pF
C _{rss}	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 42 \text{ V};$ f = 1 MHz		-	1.5	-	pF

^[1] I_D is the drain current.

Table 7. RF characteristics

RF characteristics in Ampleon production narrowband test circuit; $T_{case} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
2-Tone, o	class-AB					
V_{DS}	drain-source voltage		-	42	-	V
I _{Dq}	quiescent drain current	<u>[1</u>	<u>1]</u> _	1.3	-	Α
P _{L(AV)}	average output power	f ₁ = 860 MHz; f ₂ = 860.1 MHz	200	-	-	W
G _p	power gain	$f_1 = 860 \text{ MHz};$ $f_2 = 860.1 \text{ MHz}$	20	21	-	dB
η_{D}	drain efficiency	$f_1 = 860 \text{ MHz};$ $f_2 = 860.1 \text{ MHz}$	43	47	-	%
IMD3	third-order intermodulation distortion	f ₁ = 860 MHz; f ₂ = 860.1 MHz	-	-33	-29	dBc

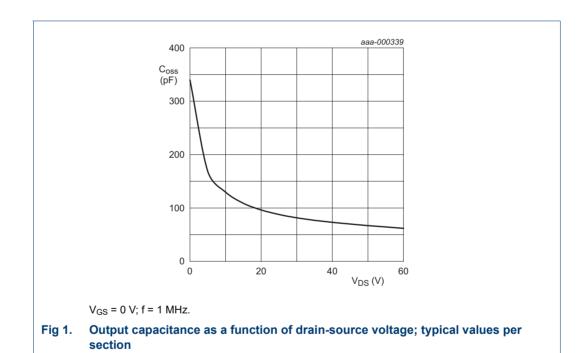
^[2] Capacitance values without internal matching.

Table 7. RF characteristics ... continued

RF characteristics in Ampleon production narrowband test circuit; $T_{case} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
DVB-T (8	k OFDM), class-AB						
V_{DS}	drain-source voltage			-	42	-	V
I_{Dq}	quiescent drain current		[1]	-	1.3	-	Α
$P_{L(AV)}$	average output power	f = 858 MHz		95	-	-	W
Gp	power gain	f = 858 MHz		20	21	-	dB
η_{D}	drain efficiency	f = 858 MHz		30	33	-	%
IMD_{shldr}	intermodulation distortion shoulder	f = 858 MHz	[2]	-	-31	-28	dBc
PAR	peak-to-average ratio	f = 858 MHz	[3]	-	8.2	-	dB

- [1] I_{Dq} for total device
- [2] Measured [dBc] with delta marker at 4.3 MHz from center frequency.
- [3] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.



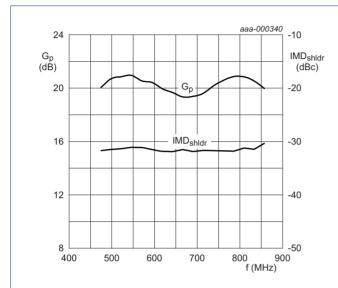
6.1 Ruggedness in class-AB operation

The BLF879P and BLF879PS are capable of withstanding a load mismatch corresponding to VSWR = 40:1 through all phases under the following conditions: $V_{DS} = 42 \text{ V}$; f = 860 MHz at rated power.

7. Application information

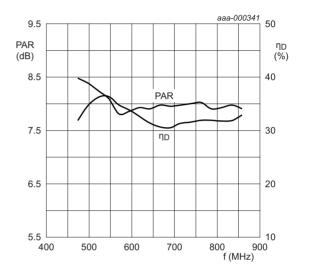
7.1 Broadband RF figures

7.1.1 DVB-T



 $P_{L(AV)}=95~W;~V_{DS}=42~V;~I_{Dq}=1.3~A;~measured~in~a~common~source~broadband~test~circuit~as~described~in~Section~8.$

Fig 2. DVB-T power gain and intermodulation distortion shoulder as function of frequency; typical values



 $P_{L(AV)}=95~W;~V_{DS}=42~V;~I_{Dq}=1.3~A;~measured~in~a~common~source~broadband~test~circuit~as~described~in~Section~8.$

Fig 3. DVB-T peak-to-average ratio and drain efficiency as function of frequency; typical values

7.2 Impedance information

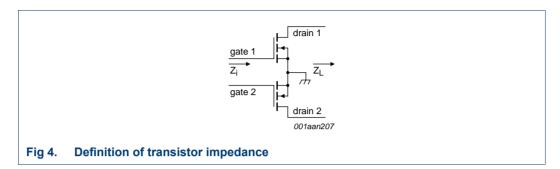
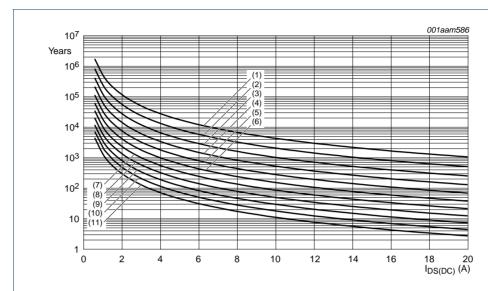


Table 8. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 42$ V and $P_{L(AV)} = 95$ W (DVB-T).

f	Z i	$\mathbf{Z_L}$
MHz	Ω	Ω
300	0.617 – j1.715	4.164 + j0.608
325	0.635 – j1.355	4.101 + j0.636
350	0.655 – j1.026	4.036 + j0.661
375	0.677 – j0.721	3.968 + j0.681
400	0.702 - j0.435	3.898 + j0.696
425	0.731 – j0.164	3.826 + j0.707
450	0.762 + j0.096	3.753 + j0.713
475	0.798 + j0.347	3.679 + j0.715
500	0.839 + j0.592	3.604 + j0.713
525	0.884 + j0.833	3.528 + j0.706
550	0.936 + j1.072	3.453 + j0.695
575	0.995 + j1.310	3.377 + j0.680
600	1.063 + j1.549	3.302 + j0.661
625	1.141 + j1.791	3.227 + j0.638
650	1.230 + j2.037	3.153 + j0.612
675	1.334 + j2.289	3.079 + j0.582
700	1.456 + j2.548	3.007 + j0.549
725	1.599 + j2.814	2.936 + j0.513
750	1.768 + j3.090	2.866 + j0.474
775	1.971 + j3.376	2.797 + j0.432
800	2.214 + j3.671	2.729 + j0.387
825	2.510 + j3.975	2.663 + j0.340
850	2.873 + j4.282	2.599 + j0.291
875	3.320 + j4.584	2.535 + j0.240
900	3.875 + j4.865	2.474 + j0.186
925	4.562 + j5.095	2.414 + j0.131
950	5.409 + j5.223	2.355 + j0.074
975	6.426 + j5.166	2.298 + j0.015
1000	7.587 + j4.807	2.243 – j0.045

7.3 Reliability



TTF (0.1 % failure fraction).

The reliability at pulsed conditions can be calculated as follows: TTF (0.1 %) \times 1 / δ .

- (1) $T_i = 100 \, ^{\circ}C$
- (2) $T_i = 110 \, ^{\circ}C$
- (3) $T_i = 120 \, ^{\circ}C$
- (4) $T_j = 130 \, ^{\circ}C$
- (5) $T_i = 140 \, ^{\circ}C$
- (6) $T_i = 150 \, ^{\circ}\text{C}$
- (7) $T_j = 160 \, ^{\circ}C$
- (8) $T_j = 170 \, ^{\circ}\text{C}$
- (9) $T_j = 180 \, ^{\circ}C$
- (10) $T_j = 190 \, ^{\circ}C$
- (11) $T_i = 200 \, ^{\circ}C$

Fig 5. BLF879P; BLF879PS electromigration (I_{DS(DC)}, total device)

8. Test information

Table 9. List of components

For test circuit, see Figure 6, Figure 7 and Figure 8.

Component	Description	Value		Remarks
B1, B2	semi rigid coax	25 $Ω$; 49.5 mm		UT-090C-25 (EZ 90-25)
C1	multilayer ceramic chip capacitor	12 pF	[1]	
C2, C3, C4, C5, C6	multilayer ceramic chip capacitor	8.2 pF	[1]	
C7	multilayer ceramic chip capacitor	6.8 pF	[2]	
C8	multilayer ceramic chip capacitor	2.7 pF	[2]	
C9	multilayer ceramic chip capacitor	2.2 pF	[2]	
C10, C13, C14	multilayer ceramic chip capacitor	100 pF	<u>[3]</u>	
C11, C12	multilayer ceramic chip capacitor	10 pF	[2]	
C15, C16	multilayer ceramic chip capacitor	4.7 μF, 50 V		Kemet C1210X475K5RAC-TU or capacitor of same quality.
C17, C18, C23, C24	multilayer ceramic chip capacitor	100 pF	[2]	
C19, C20	multilayer ceramic chip capacitor	10 μF, 50 V		TDK C570X7R1H106KT000N or capacitor of same quality.
C21, C22	electrolytic capacitor	470 μF, 63 V		
C30	multilayer ceramic chip capacitor	10 pF	<u>[4]</u>	
C31	multilayer ceramic chip capacitor	9.1 pF	<u>[4]</u>	
C32	multilayer ceramic chip capacitor	3.9 pF	<u>[4]</u>	
C33, C34, C35	multilayer ceramic chip capacitor	100 pF	<u>[4]</u>	
C36, C37	multilayer ceramic chip capacitor	4.7 μF, 50 V		TDK C4532X7R1E475MT020U or capacitor of same quality.
L1	microstrip	-	<u>[5]</u>	(W × L) 15 mm × 13 mm
L2	microstrip	-	<u>[5]</u>	(W \times L) 5 mm \times 26 mm
L3, L32	microstrip	-	<u>[5]</u>	(W \times L) 2 mm \times 49.5 mm
L4	microstrip	-	<u>[5]</u>	(W \times L) 1.7 mm \times 3.5 mm
L5	microstrip	-	<u>[5]</u>	(W \times L) 2 mm \times 9.5 mm
L30	microstrip	-	<u>[5]</u>	(W \times L) 5 mm \times 13 mm
L31	microstrip	-	<u>[5]</u>	(W \times L) 2 mm \times 11 mm
L33	microstrip	-	<u>[5]</u>	(W \times L) 2 mm \times 3 mm
R1, R2	wire resistor	10 Ω		
R3, R4	SMD resistor	5.6 Ω		0805
R5, R6	wire resistor	100 Ω		
R7, R8	potentiometer	10 kΩ		

^[1] American technical ceramics type 800R or capacitor of same quality.

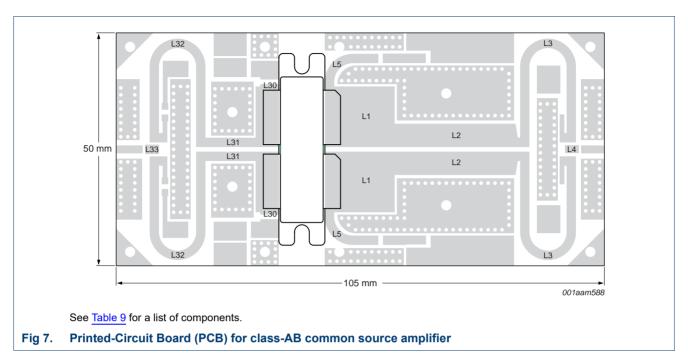
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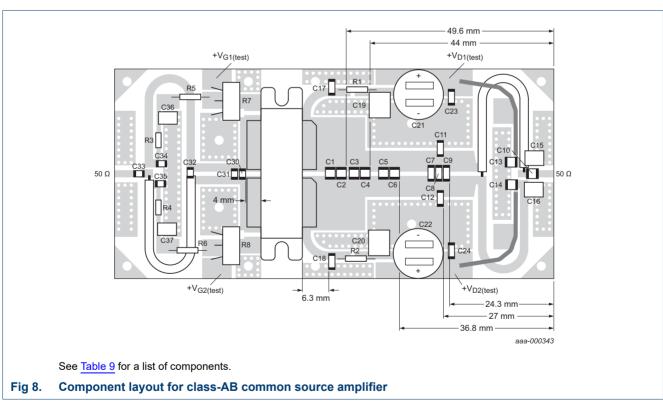
American technical ceramics type 800B or capacitor of same quality.

^[3] American technical ceramics type 180R or capacitor of same quality.

^[4] American technical ceramics type 100A or capacitor of same quality.

^[5] Printed-Circuit Board (PCB): Taconic RF35; ε_r = 3.5 F/m; height = 0.762 mm; Cu (top/bottom metallization); thickness copper plating = 35 μ m.





9. Package outline

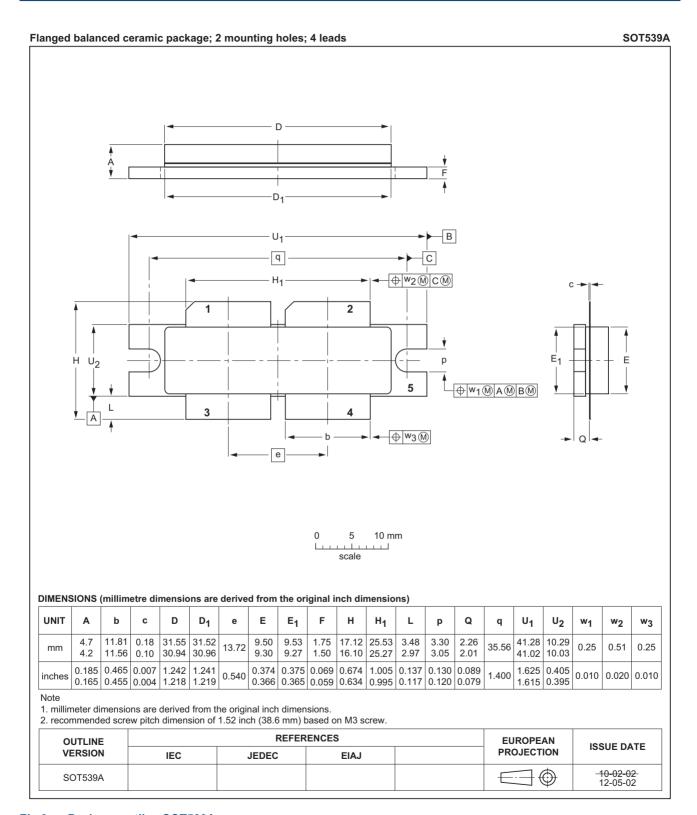


Fig 9. Package outline SOT539A

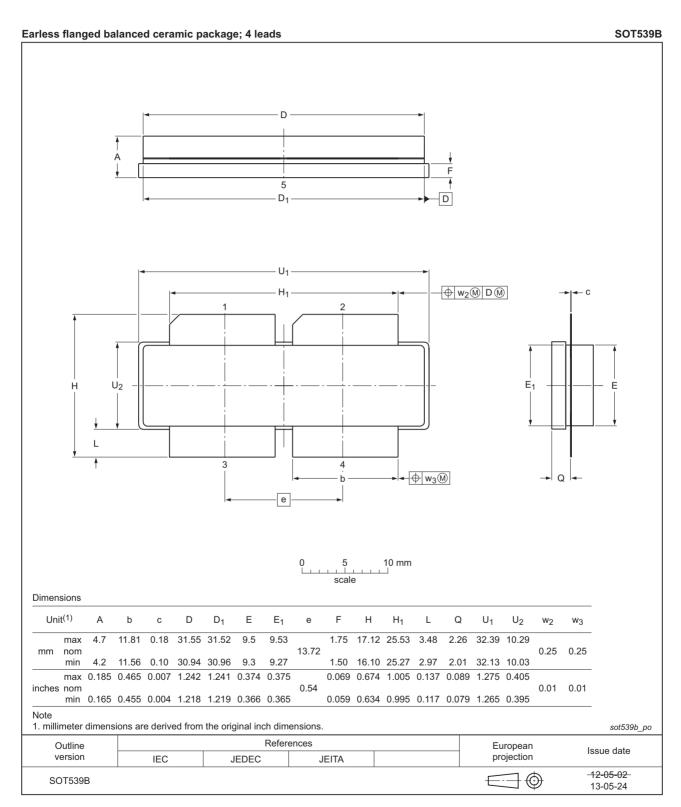


Fig 10. Package outline SOT539A

BLF879P; BLF879PS

UHF power LDMOS transistor

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Abbreviations

Table 10. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
DVB-T	Digital Video Broadcast - Terrestrial
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
TTF	Time-To-Failure
UHF	Ultra High Frequency
VSWR	Voltage Standing-Wave Ratio

12. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BLF879P_BLF879PS#4	20150901	Product data sheet	-	BLF879P_BLF879PS v.3		
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 					
BLF879P_BLF879PS v.3	20130712	Product data sheet	-	BLF879P_BLF879PS v.2		
BLF879P_BLF879PS v.2	20120725	Product data sheet	-	BLF879P v.1		
BLF879P v.1	20110823	Product data sheet	-	-		

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13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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UHF power LDMOS transistor

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